# Dual 2 A, 1.2 V, Slew Rate Controlled Load Switch

### **DESCRIPTION**

SiP32413, SiP32414 and SiP32416 are slew rate controlled load switches that is designed for 1.1 V to 5.5 V operation.

The devices guarantee low switch on-resistance at 1.2 V input. SiP32413 and SiP32414 feature a controlled soft-on slew rate of typical 150  $\mu$ s that limits the inrush current for designs of capacitive load or noise sensitive loads. SiP32416 features a longer slew rate of typical 2.5 ms to keep the peak of the inrush current even lower.

The devices feature a low voltage control logic interface (On/Off interface) that can interface with low voltage digital control without extra level shifting circuit. The SiP32414 and SiP32416 also integrate output discharge switches that enable fast shutdown load discharge. When the switches are off, they provide the reverse blocking to prevent high current flowing into the power source.

All SiP32413, SiP32414 and SiP32416 are available in TDFN8 2 mm x 2 mm package. Each switch in each device can support over 2 A of continuous current.

### **FEATURES**

Halogen-free according to IEC 61249-2-21 definition



COMPLIANT

**HALOGEN** 

FREE

- 1.1 V to 5.5 V operation voltage range
- 62 mΩ typical from 2 V to 5 V
- Low R<sub>ON</sub> down to 1.2 V
  - Slew rate controlled turn-on: 150 μs at 3.6 V for SiP32413, SiP32414 2.5 ms at 3.6 V for SiP32416
- Fast shutdown load discharge for SiP32414 and SiP32416
- Low quiescent current
   1 μA when disabled
   6.7 μA at V<sub>IN</sub> = 1.2 V
- Switch off reversed blocking
- Compliant to RoHS Directive 2002/95/EC

### **APPLICATIONS**

- · Cellular phones
- Portable media players
- · Digital camera
- GPS
- Computers
- · Portable instruments and healthcare devices

### **TYPICAL APPLICATION CIRCUIT**

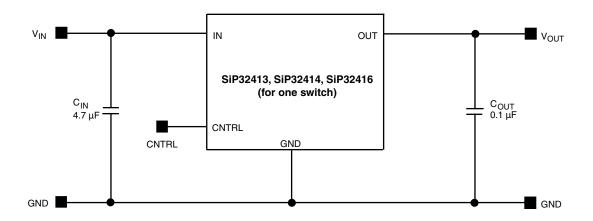


Figure 1 - SiP32413, SiP32414, SiP32416 Typical Application Circuit

# SiP32413, SiP32414, SiP32416

# Vishay Siliconix



ORDERING INFORMATION						
Temperature Range Package Marking Part Number						
- 40 °C to 85 °C		AA	SiP32413DNP-T1-GE4			
	TDFN8 2 mm x 2 mm	AB SiP32414DNP-T1-GE4	SiP32414DNP-T1-GE4			
	2 mm X 2 mm	AG	SiP32416DNP-T1-GE4			

Note:

GE4 denotes halogen-free and RoHS compliant

ABSOLUTE MAXIMUM RATINGS				
Parameter	Limit	Unit		
Supply Input Voltage (V <sub>IN</sub> )	- 0.3 to 6			
Enable Input Voltage (V <sub>EN</sub> )	- 0.3 to 6	V		
Output Voltage (V <sub>OUT</sub> )	- 0.3 to 6			
Maximum Continuous Switch Current (I <sub>max.</sub> )	2.4	Α		
Maximum Pulsed Current (Pulsed at 1 ms, 10 % Duty Cycle)	3			
ESD Rating (HBM)	4000	V		
Storage Temperature (T <sub>stg</sub> )	- 65 to 150	°C		
Thermal Resistance $(\theta_{JA})^a$	95	°C/W		
Power Dissipation (P <sub>D</sub> ) <sup>a, b</sup>	580	mW		

### Notes:

- a. Device mounted with all leads and power pad soldered or welded to PC board, see PCB layout.
- b. Derate 10.5 mW/ $^{\circ}$ C above T<sub>A</sub> = 70  $^{\circ}$ C, see PCB layout.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating/conditions for extended periods may affect device reliability.

RECOMMENDED OPERATING RANGE				
Parameter	Limit	Unit		
Input Voltage Range (V <sub>IN</sub> )	1.1 to 5.5	V		
Operating Junction Temperature Range (T <sub>J</sub> )	- 40 to 125	°C		



		Test Conditions Unless Specified V <sub>IN</sub> = 5 V, T <sub>A</sub> = -40 °C to 85 °C	Limits - 40 °C to 85 °C				
Parameter	Symbol	(Typical values are at T <sub>A</sub> = 25 °C)	Min.a	Typ.b	Max. <sup>a</sup>	Unit	
Operating Voltage <sup>c</sup>	V <sub>IN</sub>		1.1	-	5.5	V	
· · · · · · · · · · · · · · · · · · ·		V <sub>IN</sub> = 1.2 V, CNTRL = active	-	6.7	14		
		V <sub>IN</sub> = 1.8 V, CNTRL = active	-	14	24		
Outcome Outcome		V <sub>IN</sub> = 2.5 V, CNTRL = active	-	25	40		
Quiescent Current	ΙQ	V <sub>IN</sub> = 3.6 V, CNTRL = active	-	40	60		
		V <sub>IN</sub> = 4.3 V, CNTRL = active	-	52	75	μΑ	
		V <sub>IN</sub> = 5 V, CNTRL = active	-	71	99	7	
Off Supply Current	I <sub>Q(off)</sub>	CNTRL = inactive, OUT = open	-	-	1	1	
Off Switch Current	I <sub>DS(off)</sub>	CNTRL = inactive, OUT = 0	-	-	1		
Reverse Blocking Current	I <sub>RB</sub>	$V_{OUT} = 5 \text{ V}, V_{IN} = 1.2 \text{ V}, V_{EN} = \text{inactive}$	-	-	10	=	
		V <sub>IN</sub> = 1.2 V, I <sub>L</sub> = 100 mA, T <sub>A</sub> = 25 °C	-	66	76	1	
		V <sub>IN</sub> = 1.8 V, I <sub>L</sub> = 100 mA, T <sub>A</sub> = 25 °C	-	62	72	mΩ	
		V <sub>IN</sub> = 2.5 V, I <sub>L</sub> = 100 mA, T <sub>A</sub> = 25 °C	-	62	72		
On-Resistance	R <sub>DS(on)</sub>	V <sub>IN</sub> = 3.6 V, I <sub>L</sub> = 100 mA, T <sub>A</sub> = 25 °C	-	62	72		
		V <sub>IN</sub> = 4.3 V, I <sub>L</sub> = 100 mA, T <sub>A</sub> = 25 °C	-	62	72		
		V <sub>IN</sub> = 5 V, I <sub>L</sub> = 100 mA, T <sub>A</sub> = 25 °C	-	62	72	1	
On-Resistance TempCoefficient	TC <sub>RDS</sub>		-	3900	-	ppm/°	
	- 1103	V <sub>IN</sub> = 1.2 V	-	-	0.3		
		V <sub>IN</sub> = 1.8 V	-	-	0.4 <sup>d</sup>		
		V <sub>IN</sub> = 2.5 V	-	-	0.5 <sup>d</sup>		
CNTRL Input Low Voltage <sup>c</sup>	V <sub>IL</sub>	V <sub>IN</sub> = 3.6 V	-	-	0.6 <sup>d</sup>		
		V <sub>IN</sub> = 4.3 V	-	-	0.7 <sup>d</sup>		
		V <sub>IN</sub> = 5 V	-	-	0.8 <sup>d</sup>	→	
		V <sub>IN</sub> = 1.2 V	0.9 <sup>d</sup>	-	-	V	
		V <sub>IN</sub> = 1.8 V	1.2 <sup>d</sup>	-	-	-	
CNTDL Input Lligh Voltage	V	V <sub>IN</sub> = 2.5 V	1.4 <sup>d</sup>	-	-		
CNTRL Input High Voltage <sup>c</sup>	V <sub>IH</sub>	V <sub>IN</sub> = 3.6 V	1.6 <sup>d</sup>	-	-		
		V <sub>IN</sub> = 4.3 V	1.7 <sup>d</sup>	-	-	_	
		V <sub>IN</sub> = 5 V	1.8	-	-		
EN Input Leakage	I <sub>SINK</sub>	V <sub>EN</sub> = 5.5 V	1	-	1	μΑ	
Output Pulldown Resistance	R <sub>PD</sub>	CNTRL = inactive, T <sub>A</sub> = 25 °C (SiP32414 and SiP32416 only)	-	217	280	Ω	
Output Turn-On Delay Time	t <sub>d(on)</sub>	-	-	140	210	μs	
() Lithuit Lirn-()n Risa Lima I	P32413, t <sub>(on)</sub>	]	80	150	220		
Output Turn-Off Delay Time	t <sub>d(off)</sub>	V 00VD 400		0.27	1		
Output Turn-On Delay Time	t <sub>d(on)</sub>	$C_{LOAD} = 0.1 \mu F$ , $T_A = 25  ^{\circ}C$	-	2	-		
Output Turn-On Rise Time Sil	P32416 t <sub>(on)</sub>	7		2.5	3.8	ms	
Output Turn-Off Delay Time	t <sub>d(off)</sub>	1	-	-	0.001	7	

- a. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum.
- b. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
- c. For  $V_{\text{IN}}$  outside this range consult typical EN threshold curve.
- d. Not tested, guarantee by design.

### **PIN CONFIGURATION**

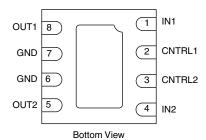


Figure 2 - TDFN8 2 mm x 2 mm Package

PIN DESCRIPTION				
Pin Number	Name	Function		
1	IN1	This is the input pin of the switch side 1		
2	CNTRL1	This is the control pin of the switch side 1		
3	CNTRL2	This is the control pin of the switch side 2		
4	IN2	This is the input pin of the switch side 2		
5	OUT2	This is the output pin of the switch side 2		
6	GND	Ground connection		
7	GND	Ground connection		
8	OUT1	This is the output pin of the switch side 1		

TRUTH TABLE SiP32413						
CNTRL1 CNTRL2 SW1 SW2						
0	0	ON	OFF			
0	1	ON	ON			
1	0	OFF	OFF			
1	1	OFF	ON			

TRUTH TABLE SiP32414, SiP32416						
CNTRL1 CNTRL2 SW1 SW2						
0	0	OFF	OFF			
0	1	OFF	ON			
1	0	ON	OFF			
1	1	ON	ON			

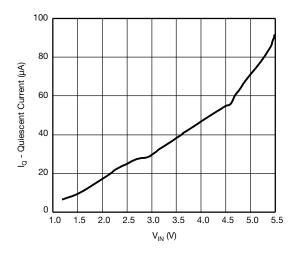


Figure 3 - Quiescent Current vs. Input Voltage

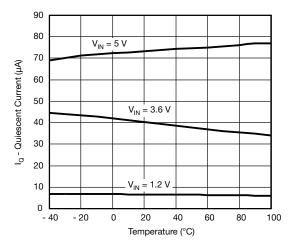


Figure 4 - Quiescent Current vs. Temperature

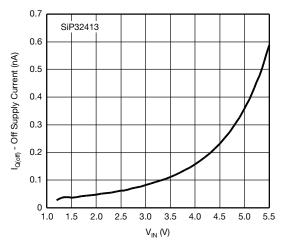


Figure 5 - SiP32413 Off Supply Current vs. VIN

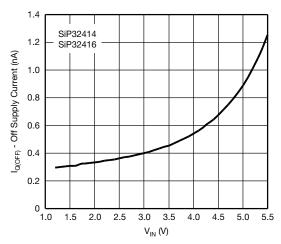


Figure 7 - SiP32414 and SiP32416 Off Supply Current vs. VIN

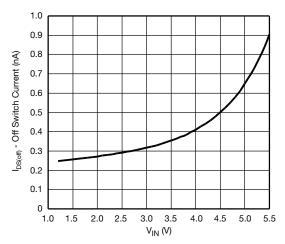


Figure 9 - Off Switch Current vs. Input Voltage

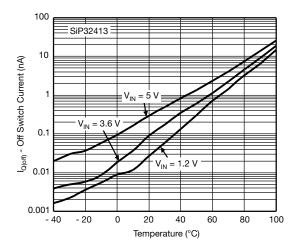


Figure 6 - SiP32414 Off Supply Current vs. Temperature

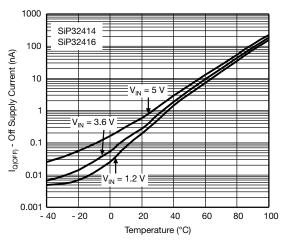


Figure 8 - SiP32414 and SiP32416 Off Supply Current vs. Temperature

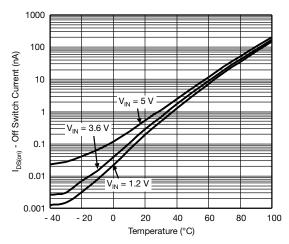


Figure 10 - Off Switch Current vs. Temperature

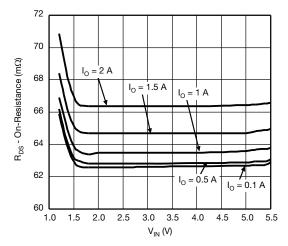


Figure 11 - R<sub>DS(on)</sub> vs. Input Voltage

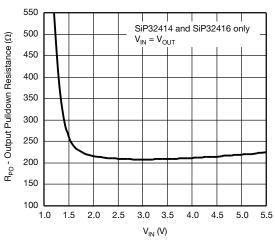


Figure 13 - SiP32414 and SiP32416 Output Pull Down vs. Input Voltage

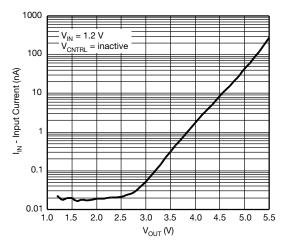


Figure 15 - Reverse Blocking Current vs. Output Voltage

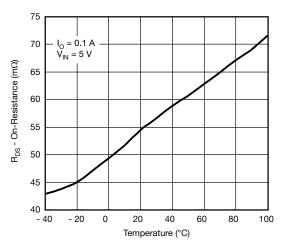


Figure 12 - R<sub>DS(on)</sub> vs. Temperature

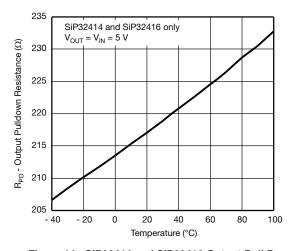


Figure 14 - SiP32414 and SiP32416 Output Pull Down vs. Temperature

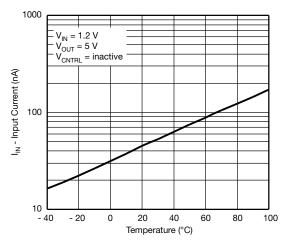


Figure 16 - Reverse Blocking Current vs. Temperature

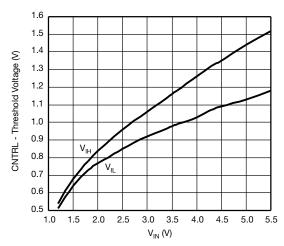


Figure 17 - CNTRL Threshold Voltage vs. Input Voltage

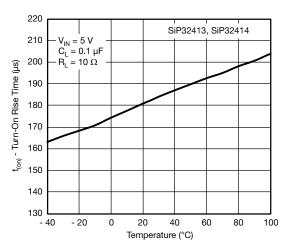


Figure 19 - SiP32413 and SiP32414 Rise Time vs. Temperature

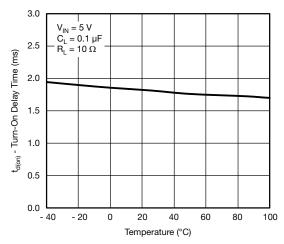


Figure 21 - SiP32416 Turn-On Delay Time vs. Temperature

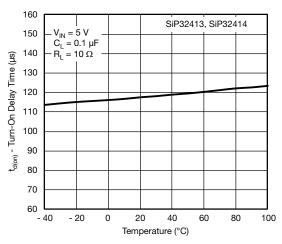


Figure 18 - SiP32413 and SiP32414 Turn-On Delay Time vs. Temperature

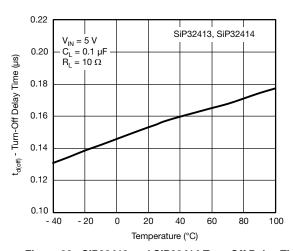


Figure 20 - SiP32413 and SiP32414 Turn-Off Delay Time vs. Temperature

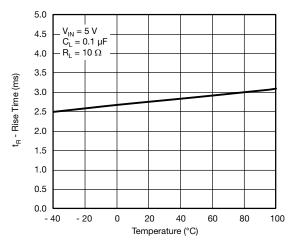


Figure 22 - SiP32416 Rise Time vs. Temperature

### TYPICAL CHARACTERISTICS (internally regulated, 25 °C, unless otherwise noted)

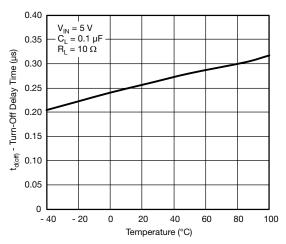


Figure 23 - SiP32416 Turn-Off Delay Time vs. Temperature

### **TYPICAL WAVEFORMS**

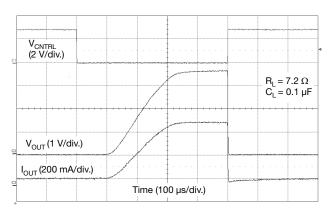


Figure 24 - SiP32413 Channel 1 Switching  $(V_{IN} = 3.6 \text{ V}, R_L = 7.2 \Omega)$ 

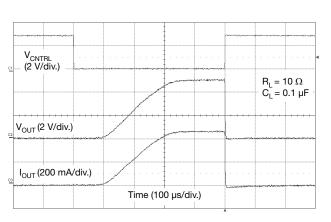


Figure 26 - SiP32413 Channel 1 Switching  $(\mathsf{V_{IN}}=5~\mathsf{V},~\mathsf{R_L}=10~\Omega)$ 

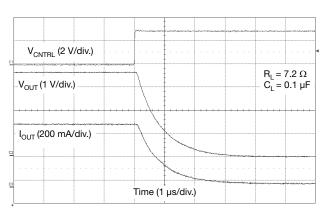


Figure 25 - SiP32413 Channel 1 Turn-Off  $(V_{IN} = 3.6 \text{ V}, R_L = 7.2 \Omega)$ 

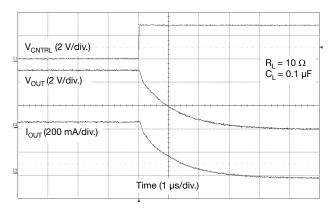


Figure 27 - SiP32413 Channel 1 Turn-Off  $(V_{IN} = 5 V, R_L = 10 \Omega)$ 



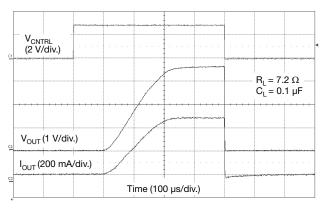
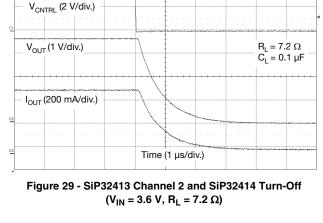


Figure 28 - SiP32413 Channel 2 and SiP32414 Switching  $(V_{IN} = 3.6 \text{ V}, R_L = 7.2 \Omega)$ 



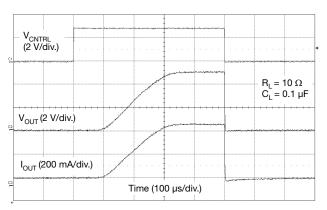


Figure 30 - SiP32413 Channel 2 and SiP32414 Switching ( $V_{IN}$  = 5 V,  $R_L$  = 10  $\Omega$ )

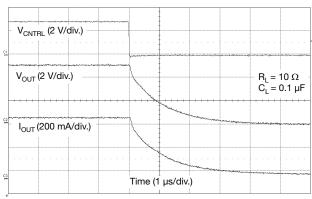


Figure 31 - SiP32413 Channel 2 and SiP32414 Turn-Off  $(V_{IN}=5~V,~R_L=10~\Omega)$ 

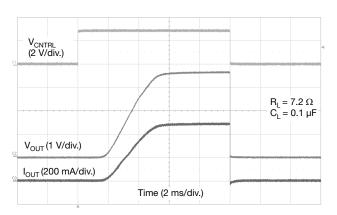


Figure 32 - SiP32416 Switching  $(V_{IN} = 3.6 \text{ V}, R_L = 7.2 \Omega)$ 

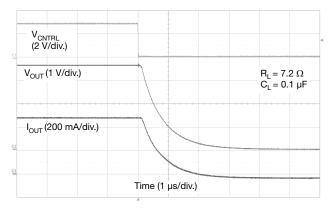
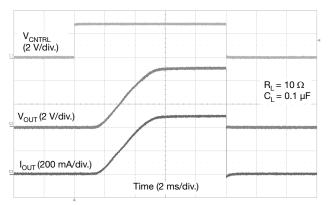


Figure 33 - SiP32416 Turn-Off  $(V_{IN} = 3.6 \text{ V}, R_L = 7.2 \Omega)$ 





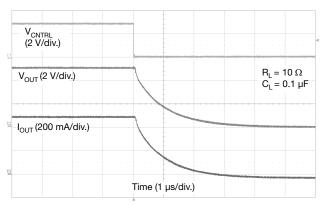


Figure 34 - SiP32416 Switching  $(V_{IN} = 5 V, R_{L} = 10 \Omega)$ 

Figure 35 - SiP32416 Turn-Off  $(V_{IN} = 5 V, R_{L} = 10 \Omega)$ 

### **BLOCK DIAGRAM**

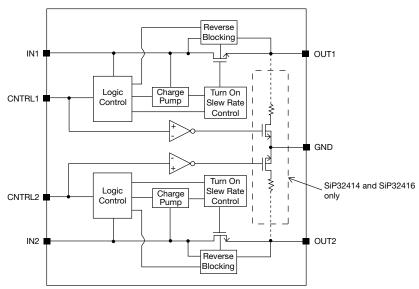
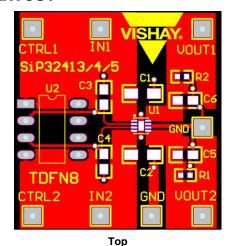


Figure 36 - Functional Block Diagram

### **PCB LAYOUT**



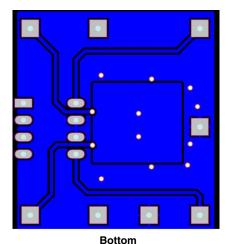


Figure 37 - PCB Layout for TDFN8 2 mm x 2 mm (type: FR4, size: 1.2" x 1.3", thickness: 0.062", copper thickness: 2 oz.)



### **DETAILED DESCRIPTION**

SiP32413, SiP32414 and SiP32416 are dual n-channel power MOSFETs designed as high side load switch with slew rate control to prevent in-rush current. Once enable the device charges the gate of the power MOSFET to 5 V gate to source voltage while controlling the slew rate of the turn on time. The mostly constant gate to source voltage keeps the on resistance low through out the input voltage range. For SiP32414, when disable the output discharge circuit turns on to help pull the output voltage to ground more quickly. For all parts, in disable mode, the reverse blocking circuit is activated to prevent current from going back to the input in case the output voltage is higher than the input voltage. Input voltage is needed for the reverse blocking circuit to work properly, it can be as low as V<sub>IN(min.)</sub>.

### **APPLICATION INFORMATION**

### **Input Capacitor**

While bypass capacitors on the inputs are not required,  $2.2 \mu F$  or larger capacitors for  $C_{IN}$  is recommended in almost all applications. The bypass capacitors should be placed as physically close as possible to the device's input to be effective in minimizing transients on the input. Ceramic capacitors are recommended over tantalum because of their ability to withstand input current surges from low impedance sources such as batteries in portable devices.

### **Output Capacitor**

A 0.1  $\mu F$  capacitor or larger across  $V_{OUT}$  and GND is recommended to insure proper slew operation. C<sub>OUT</sub> may be increased without limit to accommodate any load transient condition with only minimal affect on the turn on slew rate time. There are no ESR or capacitor type requirement.

The CNTRL pins are compatible with both TTL and CMOS logic voltage levels.

### **Protection Against Reverse Voltage Condition**

SiP32413, SiP32414 and SiP32416 contain reverse blocking circuitries to protect the current from going to the input from the output in case where the output voltage is higher than the input voltage when the main switch is off. Supply voltages as low as the minimum required input voltage are necessary for these circuitries to work properly.

### **Thermal Considerations**

All three parts are designed to maintain constant output load current. Due to physical limitations of the layout and assembly of the device the maximum switch current is 2.4 A, as stated in the Absolute Maximum Ratings table. However, another limiting characteristic for the safe operating load current is the thermal power dissipation of the package. To obtain the highest power dissipation (and a thermal resistance of 95) the power pad of the device should be connected to a heat sink on the printed circuit board.

The maximum power dissipation in any application is dependant on the maximum junction temperature,  $T_{J(max.)}$  = 125 °C, the junction-to-ambient thermal resistance for the TDFN4 1.2 mm x 1.6 mm package,  $\theta_{J-A} = 95$  °C/W, and the ambient temperature, TA, which may be formulaically

$$P (max.) = \frac{T_J (max.) - T_A}{\theta_{J-A}} = \frac{125 - T_A}{95}$$

It then follows that, assuming an ambient temperature of 70 °C, the maximum power dissipation will be limited to about 580 mW.

So long as the load current is below the 2.4 A limit, the maximum continuous switch current becomes a function two things: the package power dissipation and the R<sub>DS(ON)</sub> at the ambient temperature.

As an example let us calculate the worst case maximum load current at  $T_A = 70$  °C. The worst case  $R_{DS(ON)}$  at 25 °C occurs at an input voltage of 1.2 V and is equal to 75 m $\Omega$ . The R<sub>DS(ON)</sub> at 70 °C can be extrapolated from this data using the following formula:

 $R_{DS(ON)}$  (at 70 °C) =  $R_{DS(ON)}$  (at 25 °C) x (1 +  $T_C$  x  $\Delta T$ ) Where  $T_C$  is 3400 ppm/°C. Continuing with the calculation

 $R_{DS(ON)}$  (at 70 °C) = 75 m $\Omega$  x (1 + 0.0034 x (70 °C - 25 °C))  $= 86.5 \text{ m}\Omega$ 

The maximum current limit is then determined by

$$I_{LOAD}$$
 (max.)  $<\sqrt{\frac{P \text{ (max.)}}{R_{DS(ON)}}}$ 

which in case is 2.6 A, assuming one switch turn on at a time. Under the stated input voltage condition, if the 2.6 A current limit is exceeded the internal die temperature will rise and eventually, possibly damage the device.

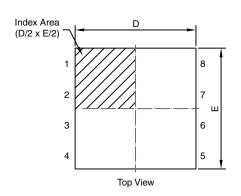
To avoid possible permanent damage to the device and keep a reasonable design margin, it is recommended to operate the device maximum up to 2.4 A only as listed in the Absolute Maximum Ratings table.

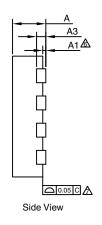
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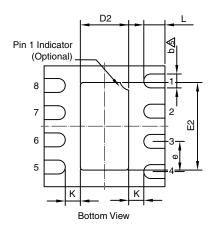




### CASE OUTLINE FOR TDFN8 2 x 2







	MILLIMETERS			INCHES		
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
Α	0.50	0.55	0.60	0.020	0.022	0.024
A1	0.00	-	0.05	0.000	-	0.002
A3	0.152 REF			0.006 REF		
b	0.18	0.23	0.28	0.007	0.009	0.011
D	1.95	2.00	2.05	0.077	0.079	0.081
D2	0.75	0.80	0.85	0.030	0.031	0.033
е	0.50 BSC			0.020 BSC		
Е	1.95	2.00	2.05	0.077	0.079	0.081
E2	1.40	1.45	1.50	0.055	0.057	0.059
K	-	0.20	-	-	0.008	-
L	0.30	0.35	0.40	0.012	0.014	0.016
ECN: C11-0033 Rev. A, 07-Feb-11						

DWG: 5997

### Note

- 1. All dimensions are in millimeters which will govern.
- 2. Max. package warpage is 0.05 mm.
- 3. Max. allowable burrs is 0.076 mm in all directions.
- 4. Pin #1 ID on top will be laser/ink marked.
- Dimension applies to meatlized terminal and is measured between 0.20 mm and 0.25 mm from terminal tip.
- Applied only for terminals.
- Applied for exposed pad and terminals.



## **Legal Disclaimer Notice**

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# **Material Category Policy**

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

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Revision: 02-Oct-12 Document Number: 91000



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

### Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов:
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001:
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



### Как с нами связаться

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